Form 1449*	Atty. Docket No.: 303.648US1	Serial No. 09/484,303
INFORMATION DISCLOSURE STATEMENT BY APPLICANT (Use several sheets if necessary)	Applicant: Kie Y. Ahn et al.	
	Filing Date: January 18, 2000	Group: 2825

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NB	3,954,570	06/04/1976	Shirk, et al.	201	15	11/11/74
NB	4,386,116	05/31/1983	Nair, et al.	427	99	12/24/81
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